



UI-TF-03050

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Milton Feng, Nick Holonyak, Jr. and Walid Hafez

Serial No. : 10/646,457

Group: 2811

Filed : August 22, 2003

For : LIGHT EMITTING DEVICE AND METHOD

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

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Sir:

Applicant submits herewith a Form PTO-1449, and copies of the documents listed thereon.

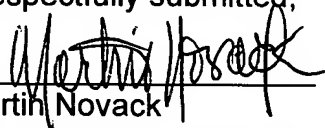
To the best of Applicant's knowledge, this Information Disclosure Statement is being filed before the first Office Action on the merits in the present application, so no fee is due under Rule 97.

The listed documents are brought to the Examiner's attention because they are known to Applicant and/or Applicant's attorney and may be considered by the Examiner to be material to the examination of this application. This submission should not be

construed as a representation that a search has been made or that no better art exists.

No inference should be made that the documents constitute prior art or are in fact material merely because they are referenced in this submission.

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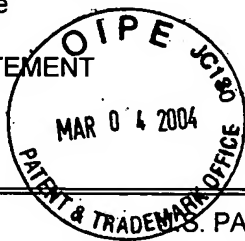
Respectfully submitted,


Martin Novack
Attorney for Applicant(s)

(F-5)

Form PTO-1449 U.S. Department of Commerce
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INFORMATION DISCLOSURE STATEMENT
BY APPLICANT
(Use several sheets if necessary)



ATTY DOCKET NO. SERIAL NO.
UI-TF-03050 10/646,457
APPLICANT: EXAMINER
M.Feng, N. Holonyak, & W. Hafez
FILING DATE: GROUP
August 22, 2003 2811

U.S. PATENT DOCUMENTS

Exam. Init.	Document Number	Date	Name	Class	Sub Class	filing date if appropriate
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FOREIGN PATENT DOCUMENTS

Init.	Document Number	Date	Country	Class	Sub Class	Translation Yes/No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER

DATE CONSIDERED

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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	W. Hafez, J.W. Lai, and M. Feng "Record f_T and $f_T + f_{MAX}$ Performance of InP/InGaAs Single Heterojunction Bipolar Transistors," Electronics Letters, May, 2003.
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